

REMARKS/ARGUMENT

The applicants' attorneys appreciate the Examiner's thorough search and remarks.

Claims 1-25 are in the application. Claims 3, 4, 8, 9 and 11 have been cancelled without prejudice.

It is acknowledged with appreciation that claims 11 and 12 have been deemed allowable if rewritten in independent form. Accordingly, claim 12 has been rewritten in independent form. Claim 1 has been amended to include the limitations of claim 11.

Claims 5-7 and 10 depend from claim 1, and, therefore, include at least its limitations.

Confirmation of allowability of claims 5-7 and 10 is requested.

Claim 13 has been rejected under 35 U.S.C. §102(b) over Wislocky et al., U.S. Patent No. 3,381,067, Reconsideration is requested.

Claim 13 calls for, in combination with other limitations, "an annular flange connected to said insulation ring at an end thereof;

a first pole being in surface-to-surface electrical contact with said first electrode, said first pole unitarily including an annular rib extending from an outer surface thereof;

a circular connector connecting said annular rib and said annular flange, thereby connecting said first pole to said flange". Wislocky et al. do not show or suggest "a circular connector connecting said annular rib and said annular flange, thereby connecting said first pole to said flange". Reconsideration of claim 13 is requested.

Claims 14-21 depend from claim 13, and, therefore, include its limitations. These claims include other limitations, which in combination with those of claim 13 are not shown or suggested by the art of record. Reconsideration is requested.

Claim 22 has been rejected under 35 U.S.C. §102(b) over Wislocky et al.
Reconsideration is requested.

Claim 22 calls for, in combination with other limitations, "an insulation ring having an interior wall annularly disposed around said semiconductor die; ... a second pole...; wherein said second pole includes an annular flange which extends radially away from said second pole and penetrates said interior wall to become embedded in said insulation ring." Wislocky et al. do not show a pole having an annular flange that penetrates the interior wall of the insulation ring as set forth in claim 22. Reconsideration is requested.

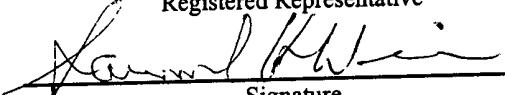
Claims 2 and 23-25 depend from claim 22, and, therefore, include its limitations. These claims include other limitations which in combination with those of claim 22 are not shown or suggested by the art of record. Reconsideration is requested.

The application is believed to be in condition for allowance. Such action is earnestly solicited.

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Asst. Commissioner for Patents, Washington, D.C. 20231, on August 8, 2002:

Samuel H. Weiner

Name of applicant, assignee or
Registered Representative

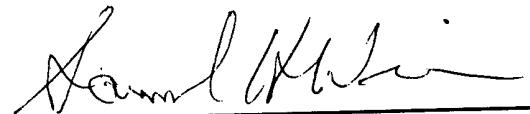

Signature

August 8, 2002

Date of Signature

SHW/KS:gl

Respectfully submitted,



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APPENDIX B
VERSION WITH MARKINGS TO SHOW CHANGES MADE
37 C.F.R. § 1.121(b)(iii) AND (c)(ii)

CLAIMS:

1. (Amended) A compression assembled semiconductor package comprising:
a semiconductor die having a first major surface and a second major surface;
a control electrode disposed on a first major surface of said semiconductor die, and first
and second electrodes disposed on first and second major surfaces respectively of said
semiconductor die;
a molded plastic insulation ring annularly disposed around said semiconductor die;
a control signal carrier extending through said molded insulation ring from the exterior
thereof and electrically connected to said control electrode;
a first pole being in surface-to-surface electrical contact with said first electrode; and
a second pole being in surface-to-surface electrical contact with said second electrode,
whereby said semiconductor die is held in place between said first pole and said second pole;
wherein said first pole comprises and forms a unitary body with a rim, said rim being
ultrasonically bonded directly to an end of said molded plastic insulation ring.
2. (Amended) The compression assembled semiconductor package of claim [1] 22,
wherein said first pole includes an annular rib which is connected to a corresponding annular
flange on an end of said molded plastic insulation ring.
12. (Amended) A compression assembled semiconductor package comprising:
a semiconductor die having a first major surface and a second major surface;
a control electrode disposed on a first major surface of said semiconductor die, and first
and second electrodes disposed on first and second major surfaces respectively of said
semiconductor die;
a molded plastic insulation ring annularly disposed around said semiconductor die;

a control signal carrier extending through said molded insulation ring from the exterior thereof and electrically connected to said control electrode;

a first pole being in surface-to-surface electrical contact with said first electrode; and
a second pole being in surface-to-surface electrical contact with said second electrode,
whereby said semiconductor die is held in place between said first pole and said second pole.
[The compression assembled semiconductor package of claim 1,] wherein said second pole comprises and forms a unitary body with a rim, said rim being ultrasonically bonded directly to an end of said molded plastic insulation ring.

22. (Amended) A compression assembled semiconductor package comprising:
a semiconductor die having a first major surface and a second major surface;
a control electrode disposed on a first major surface of said semiconductor die, and first and second electrodes disposed on first and second major surfaces respectively of said semiconductor die;
an insulation ring having an interior wall annularly disposed around said semiconductor die;
a control signal carrier extending through said insulation ring from the exterior thereof and having an end in electrical contact with said control electrode;
a first pole being in surface-to-surface electrical contact with said first electrode; and
a second pole being in surface-to-surface electrical contact with said second electrode,
whereby said semiconductor device is held in place between said first pole and said second pole;
wherein said second pole includes an annular flange which extends radially away from
said second pole and penetrates said interior wall to become at least partially embedded in said insulation ring.